

General Description

The GreenMOS[®] high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS[®] Z series is integrated with fast recovery diode (FRD) to minimize reverse recovery time. It is suitable for resonant switching topologies to reach higher efficiency, higher reliability and smaller form factor.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity




Applications

- LED lighting
- Telecom
- Adapter
- Sever
- Solar/UPS

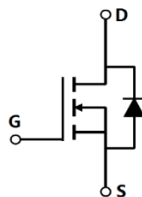
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	650	V
$I_{D, pulse}$	186	A
$R_{DS(ON), max @ V_{GS}=10V}$	40	m Ω
Q_g	107	nC
PD	360	W

Marking Information

Product Name	Package	Marking
OSG65R040HT4ZF	TO247	OSG65R040HT4Z

Package & Pin Information



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Gate-source voltage (static)	V_{GS}	± 20	V
Gate-source voltage (dynamic)		± 30	V
Continuous drain current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_D	62	A
Continuous drain current ¹⁾ , $T_C=100^{\circ}\text{C}$		39.2	
Pulsed drain current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{D, pulse}$	186	A
Continuous diode forward current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_S	62	A
Diode pulsed current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{S, pulse}$	186	A
Power dissipation ³⁾ , $T_C=25^{\circ}\text{C}$	P_D	360	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	518	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 400\text{ V}$	dv/dt	100	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 400\text{ V}$, $I_{SD}\leq I_D$	dv/dt	50	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.35	$^{\circ}\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^{\circ}\text{C/W}$

Electrical Characteristics

 at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	650			V	$V_{GS}=0\text{ V}$, $I_D=2\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	3.5		5.5	V	$V_{DS}=V_{GS}$, $I_D=2\text{ mA}$
Drain-source on-state resistance	$R_{DS(ON)}$		33	40	m Ω	$V_{GS}=10\text{ V}$, $I_D=32\text{ A}$
			79			$V_{GS}=10\text{ V}$, $I_D=32\text{ A}$, $T_j=150^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=20\text{ V}$
				-100		$V_{GS}=-20\text{ V}$
Drain-source leakage current	I_{DSS}			10	μA	$V_{DS}=650\text{ V}$, $V_{GS}=0\text{ V}$
Gate resistance	R_G		2.8		Ω	$f=1\text{ MHz}$, Open drain

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		5307		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oss}		267		pF	
Reverse transfer capacitance	C_{rss}		4.2		pF	
Effective output capacitance, energy related	$C_{o(er)}$		180		pF	$V_{GS}=0\text{ V}$, $V_{DS}=0\text{ V}-400\text{ V}$
Effective output capacitance, time related	$C_{o(tr)}$		1200		pF	
Turn-on delay time	$t_{d(on)}$		37		ns	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $R_G=2\ \Omega$, $I_D=32\text{ A}$
Rise time	t_r		12		ns	
Turn-off delay time	$t_{d(off)}$		72		ns	
Fall time	t_f		2.4		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		107		nC	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $I_D=32\text{ A}$
Gate-source charge	Q_{gs}		34		nC	
Gate-drain charge	Q_{gd}		46		nC	
Gate plateau voltage	$V_{plateau}$		7.2		V	

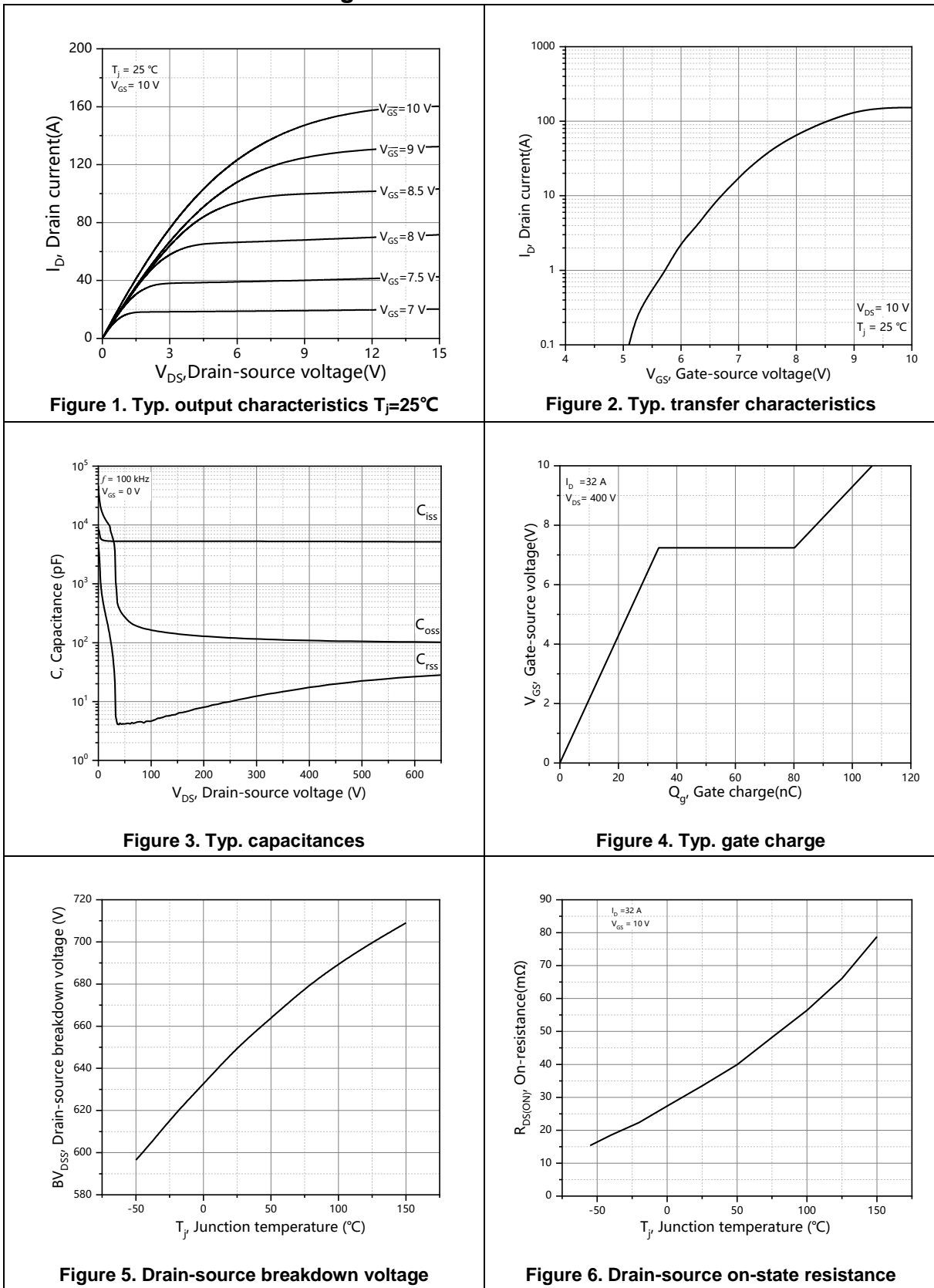
Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	$I_S=62\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		176		ns	$V_R=400\text{ V}$, $I_S=32\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		1.1		μC	
Peak reverse recovery current	I_{rrm}		10.4		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $L=80\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams



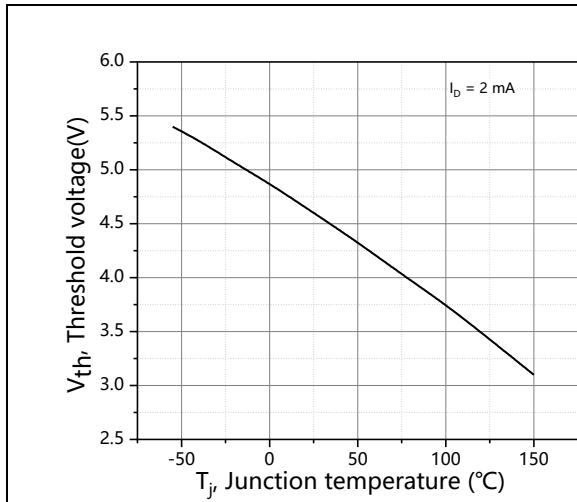


Figure 7. Threshold voltage

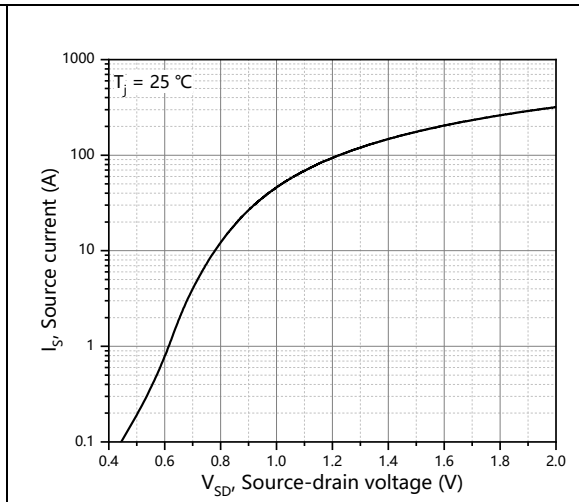


Figure 8. Forward characteristic of body diode

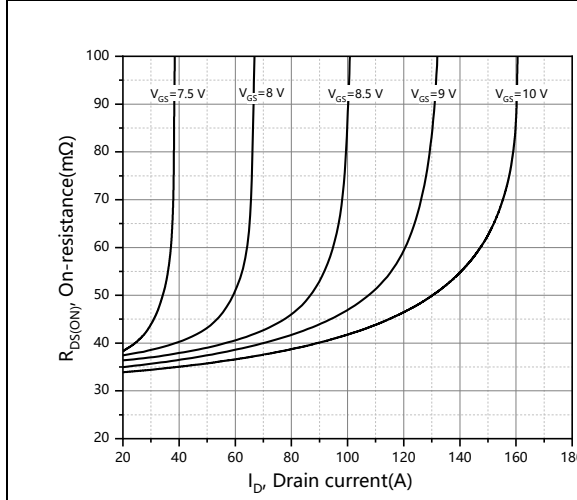


Figure 9. Drain-source on-state resistance

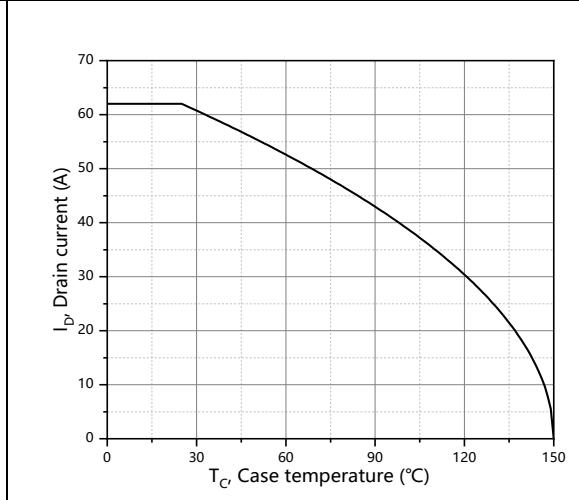


Figure 10. Drain current

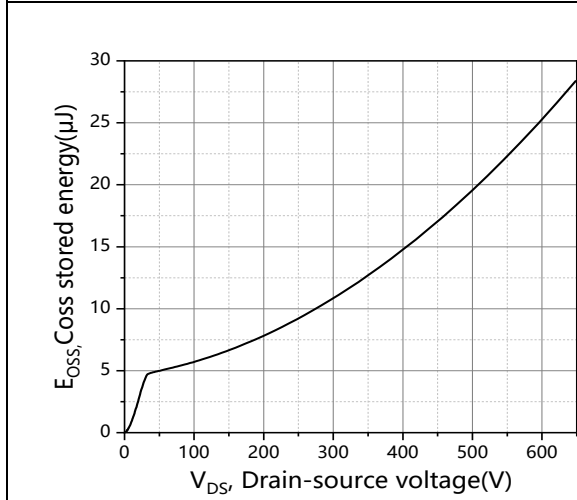


Figure 11. Typ. Coss stored energy

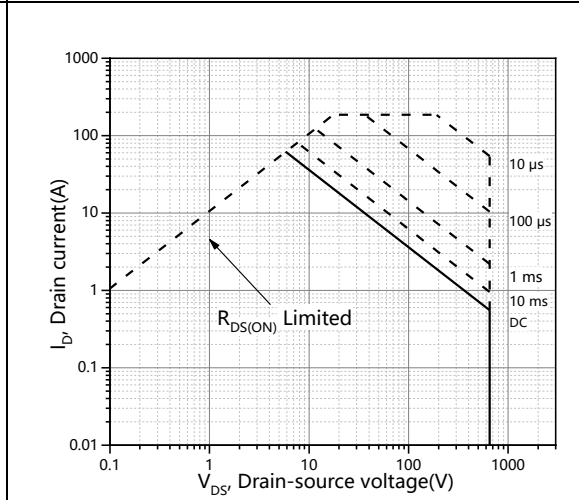
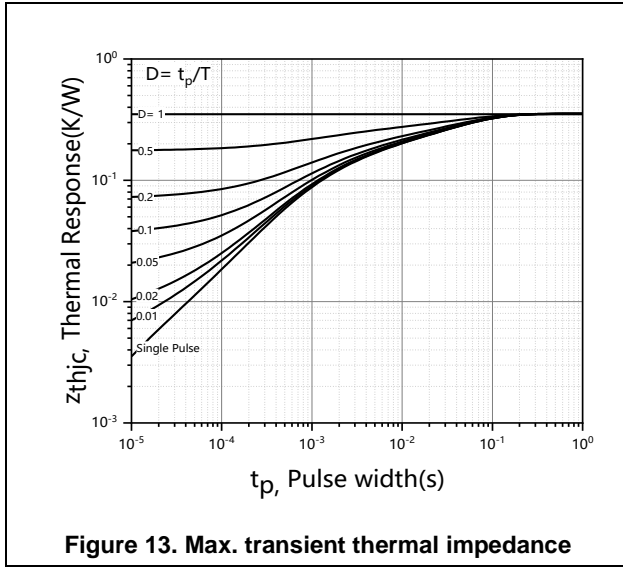


Figure 12. Safe operation area Tc=25°C



Test circuits and waveforms

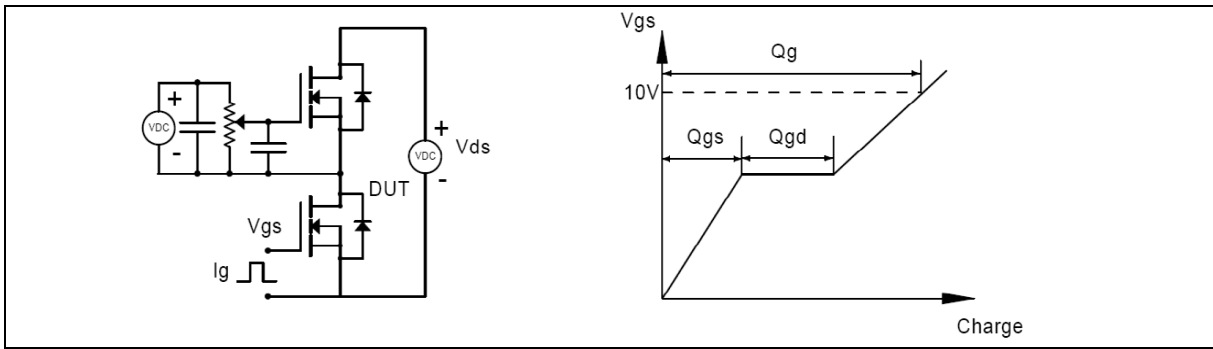


Figure 1. Gate charge test circuit & waveform

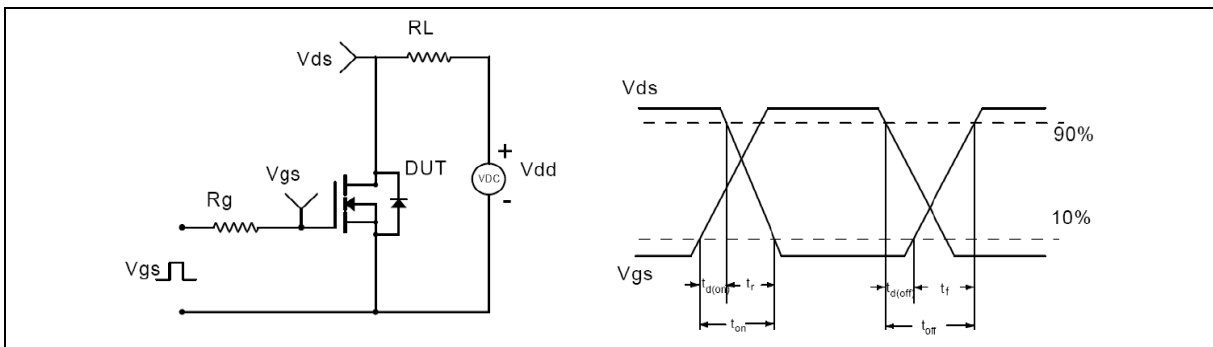


Figure 2. Switching time test circuit & waveforms

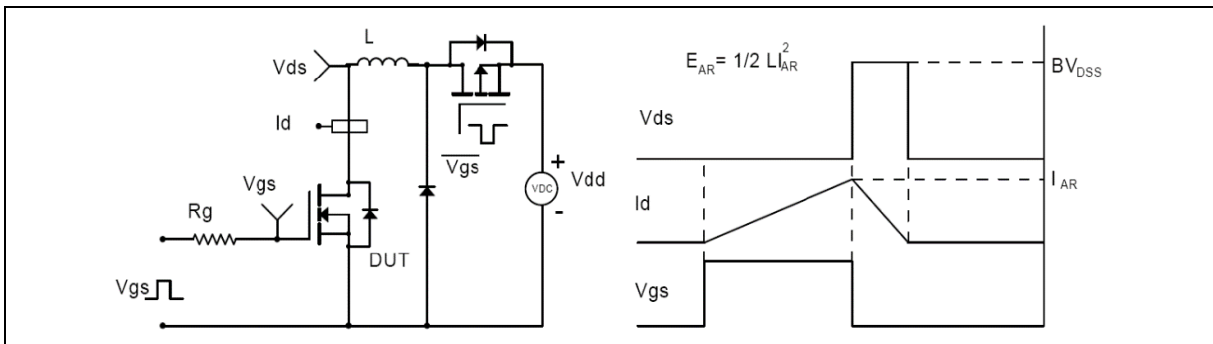


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

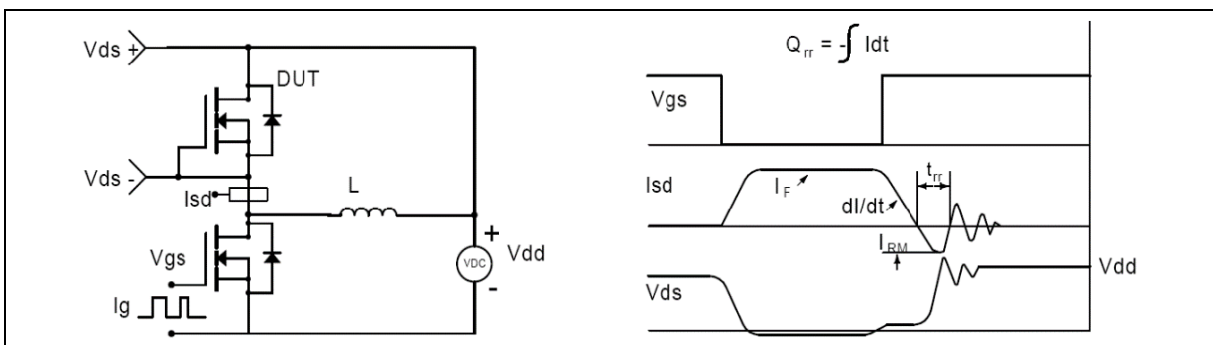
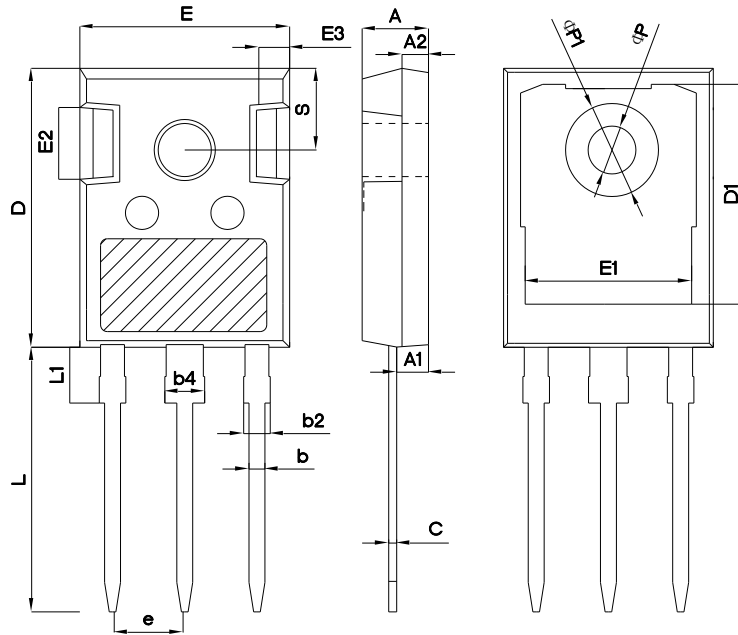


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44 BSC		
L	19.82	19.92	20.22
L1	-	-	4.30
ΦP	3.40	3.60	3.80
ΦP1	-	-	7.30
S	6.15 BSC		

Version: TO247-P package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO247-P	30	11	330	6	1980

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG65R040HT4ZF	TO247	yes	yes	yes

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Revision History

Version	Revision History	Date
V1.0	Initial release	2025-07-03